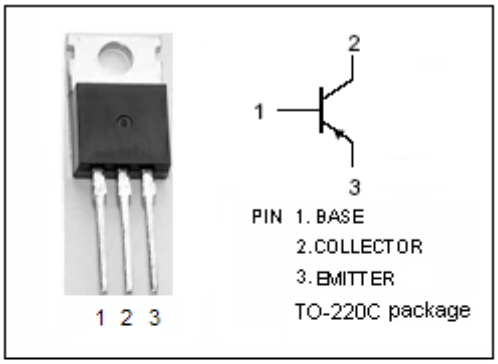
isc Silicon PNP Power Transistor 2SA614

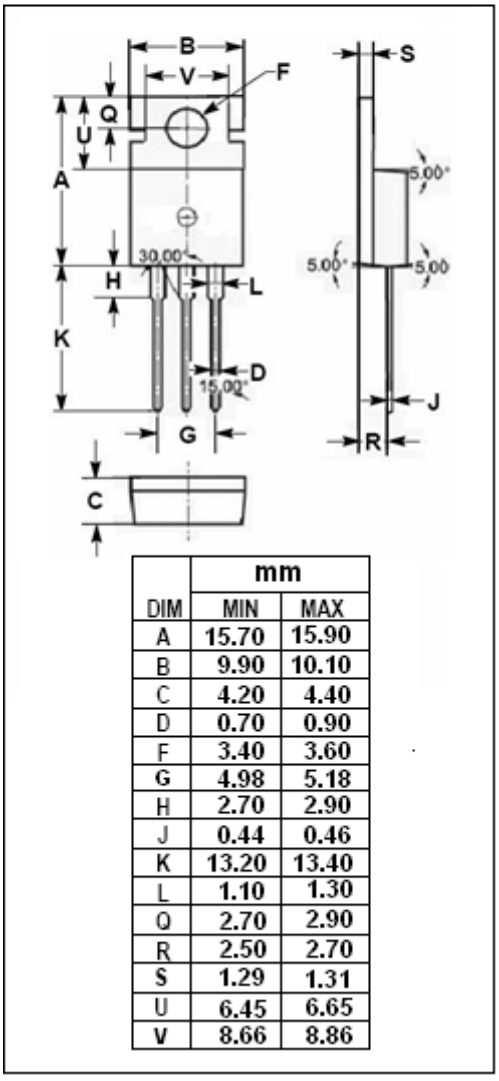


DESCRIPTION

- Collector-Emitter Breakdown Voltage-
  : $V_{(BR)CEO}$= -55V (Min.)
- Collector-Emitter Saturation Voltage-
  : $V_{CE(sat)}$= -0.5V (Max.)@ I_C= -1A
- Collector Power Dissipation-
  : P_C= 25W@ T_C= 25℃

APPLICATIONS

- Designed for medium power amplifier applications.



DIM	mm MIN	MAX
A	15.70	15.90
B	9.90	10.10
C	4.20	4.40
D	0.70	0.90
F	3.40	3.60
G	4.98	5.18
H	2.70	2.90
J	0.44	0.46
K	13.20	13.40
L	1.10	1.30
Q	2.70	2.90
R	2.50	2.70
S	1.29	1.31
U	6.45	6.65
V	8.66	8.86

ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-80	V
V_{CEO}	Collector-Emitter Voltage	-55	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-3	A
P_C	Collector Power Dissipation	25	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃

isc Silicon PNP Power Transistor 2SA614

ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= -10mA; I_B= 0	-55			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	I_C= -500μA; I_E= 0	-80			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_E= -500μA; I_C= 0	-5			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= -1A; I_B= -0.1A			-0.5	V
I_{CBO}	Collector Cutoff Current	V_{CB}= -80V; I_E= 0			-50	μA
I_{EBO}	Emitter Cutoff Current	V_{EB}= -5; I_C= 0			-50	μA
h_{FE}	DC Current Gain	I_C= -0.5A; V_{CE}= -5V	40		240	

◆ **h_{FE} Classifications**

R	O	Y
40-80	70-140	120-240